

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

Application of: Richard William CHARM et al.

Application No.: 10/689,657

Art Unit:

Filed: October 22, 2003

Examiner:

For: **PROCESS FOR THE USE OF BIS-CHOLINE  
AND TRIS-CHOLINE IN THE CLEANING  
OF QUARTZ-COATED POLYSILICON  
AND OTHER MATERIALS**

Atty Docket No.: 060937-0139  
(Former P&E No. 8317-0139)

Commissioner of Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Sir:

**SUBMISSION OF REVOCATION OF ORIGINAL POWER OF ATTORNEY  
AND GRANT OF NEW POWER OF ATTORNEY**

Enclosed is a copy of the Revocation of Original Power of Attorney and Grant of New Power of Attorney by the Assignee, EKC Technology, Inc. Assignee directs the Patent and Trademark Office to send all future correspondence to:

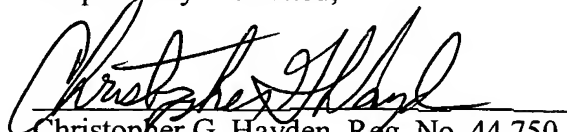
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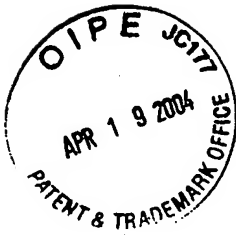
If there is any fee due in connection with the filing of this Submission, please charge the fee to Morgan, Lewis & Bockius LLP Deposit Account No. 50-0310.

Respectfully submitted,

April 19, 2004

By:

  
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## REVOCATION AND POWER OF ATTORNEY

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P. O. Box 1450  
Alexandria, Virginia 22313-1450

Sir:

EKC Technology, Inc., owner of the entire right, title and interest in, to and under the inventions described and claimed in the patent applications identified in the attached Schedule A, hereby revokes all previous powers of attorney and appoints Morgan, Lewis & Bockius LLP, Customer Number 009629, and each of them, its attorneys, to prosecute each of these patent applications, and to transact all business in the Patent and Trademark Office connected therewith.

Please direct all future correspondence to Customer No. 009629, Patent Support Unit, Morgan, Lewis & Bockius LLP, 1111 Pennsylvania Avenue, N.W., Washington, D.C. 20004, and direct all telephone calls to Morgan, Lewis & Bockius LLP at 202-739-3000.

Date: 29 March 2004 Assignee: EKC Technology, Inc.  
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## Schedule A

App. #	Title	Inventor(s)	Filing Date	New Attorney Docket No.	Former Attorney Docket No.
09/903,064	Compositions for Cleaning Organic and Plasma Etched Residues for Semiconductor Devices	Small, et al.	07/10/2001	60937-091-US	8317-091-999
09/874,330	Method of and Apparatus for Substrate Pre-Treatment	Maloney, et al.	06/06/2001	60937-111-US	8317-111-999
09/985,870	Chemical Mechanical Polishing Compositions	Small, et al.	11/06/2001	60937-114-US	8317-114-999
10/421,706	Oxalic Acid as a Semiaqueous Cleaning Product for Copper and Dielectrics	Lee, et al.	04/24/2003	60937-116-US	8317-116-999
10/193,185	Sulfoxide Pyrolid(in)one Alkanolamine Cleaner Composition	Zhou, et al.	07/12/2002	60937-118-US	8317-118-999
09/876,944	Method for the Deposition of Materials from Mesomorphous Films	Vasquez, et al.	06/08/2001	60937-120-US	8317-120-999
10/007,134	Post Etch Cleaning Composition for Dual Damascene System	Payne, et al.	12/04/2001	60937-123-US	8317-123-999
10/263,701	Photolytic Conversion Process to Form Patterned Amorphous Film	Bravo-Vasquez, et al.	10/04/2002	60937-126-US	8317-126-999
09/988,545	Cleaning Solutions Including Nucleophilic Amine Compound Having Reduction and Oxidation Potential	Lee, et al.	11/20/2001	60937-127-US	8317-127-999
10/060,109	Method and Compositions for Chemically Treating A Substrate Using Foam Technology	Patel, et al.	01/28/2002	60937-129-US	8317-129-999
10/135,695	Cleaning Solution Including Nucleophilic Amine Compound Having Reduction and Oxidation Potential	Lee, et al.	05/01/2002	60937-135-US	8317-135-999
10/448,127	Fluoride Layer and Removing Same	Melvin K. Carter	05/30/2003	60937-137-US	8317-137-999
10/689,657	Process for the Use of Bis-Choline and Tris-Choline in the Cleaning of Quartz-Coated Polysilicon and Other Materials	Charm, et al.	10/22/2003	60937-139-US	8317-139-999
10/689,620	Cleaning Compositions Containing Hydroxylamine Derivatives and Process Using Same for Residue Removal	Zhou, et al.	10/22/2003	60937-140-US	8317-140-999
10/689,616	Composition for Exfoliation Agent to be Used to Remove Resist Residues	Melvin K. Carter	10/22/2003	60937-141-US	8317-141-999
60/467,131	Reducing Oxide Loss When Using Fluoride Chemistries to Remove Post-Etch Residues in Semiconductor Processing	Lee, et al.	05/02/2003	60937-142-PR	8317-142-888

App #	Title	Inventor(s)	Filing Date	New Attorney Docket No.	Former Attorney Docket No.
10/630,301	Method for Depositing Patterned Films of Materials	Hill, et al.	07/30/2003	60937-143-US	8317-143-999
10/716,838	Methods for the Deposition of Silver and Silver Oxide Films and Patterned Films	Ruan, et al.	11/18/2003	60937-147-US	8317-147-999
10/162,679	Semiconductor Process Residue Removal Composition and Process	Lee, et al.	06/06/2002	60937-149-US	8317-149-999
60/469,826	System and Method for Cleaning Workpieces Using Supercritical Carbon Dioxide	Fury, et al.	05/13/2003	60937-150-PR	8317-150-888
10/689,043	Abrasive-Free Chemical Mechanical Polishing Composition and Polishing Process Containing Same	Yao, et al.	10/21/2003	60937-151-US	8317-151-999
10/689,042	Wet Etch of Titanium-Tungsten Film	Patel, et al.	10/21/2003	60937-152-US	8317-152-999
10/261,197	Method of Depositing Nanostructured Films with Embedded Nanopores	Svensden, et al.	09/30/2002	60937-153-US	8317-153-999
10/280,270	Hydrothermal Treatment of Nanostructured Films	Mukherjee, et al.	10/23/2002	60937-167-US	8317-167-999
10/257,469	Inhibition of Titanium Corrosion	Daviot, et al.	10/11/2002	60937-168-US	8317-168-999
10/401,405	Chemical Mechanical Polishing Composition and Process	Small, et al.	03/27/2003	60937-171-US	8317-171-999
10/688,900	Aqueous Phosphoric Acid Compositions for Cleaning Semiconductor Devices	Daviot, et al.	10/21/2003	60937-172-US	8317-172-999
10/465,906	Load Lock System for Supercritical Fluid Cleaning	Fury, et al.	06/18/2003	60937-175-US	8317-175-999
10/465,905	Automated Dense Phase Fluid Cleaning System	Fury, et al.	06/18/2003	60937-176-US	8317-176-999
60/455,439	Residue Removers for Electrohydrodynamic Cleaning of Semiconductors	Robert J. Small	03/18/2003	60937-178-PR	8317-178-888
10/361,822	Free Radical-Forming Activator Attached to Solid and Used to Enhance CMP Formulations	Scott, et al.	02/11/2003	60937-179-US	8317-179-999
10/377,533	Titanium Carboxylate Films for Use in Semiconductor Processing	Hill, et al.	02/26/2003	60937-182-US	8317-182-999
10/422,860	Method of Making Barrier Layers	Maloney, et al.	05/20/2003	60937-183-US	8317-183-999
60/463,739	Remover Formulatioi Containing Fluoride for Use During Semiconductor Manufacturing	Hirasawa, et al.	04/18/2003	60937-185-PR	8317-185-888
60/464,125	Cleaning Composition for Removing Resists and Manufacturing Method of Semiconductor Devices	Hirasawa, et al.	04/21/2003	60937-186-PR	8317-186-888
10/422,212	Deposition of Permanent Polymer Structures for OLED Fabrication	Roman, et al.	04/23/2003	60937-187-US	8317-187-999

App. #	Title	Inventor(s)	Filing Date	New Attorney Docket No.	Former Attorney Docket No.
10/442,858	Seimiconductor Process Residue Removal Composition and Process	Wai Mun Lee	05/20/2003	60937-189-US	8317-189-999
10/630,300	Cleaning Compositions and Method of Use Thereof	Wai Mun Lee	07/30/2003	60937-194-US	8317-194-999
60/518,337	Compositions and Methods for Rapidly Removing Overfilled Substrates	Chelle, et al.	11/10/2003	60937-200-PR	8317-200-888
10/690,623	CMP Method for Copper, Tungsten, Titanium, Polysilicon, and Other Substrates Using Organosulfonic Acids as Oxidizers	Carter, et al.	10/23/2003	60937-202-US	8317-202-999
60/494,954	Periodic Acid Compositions for Polishing Nobel Metal/High K Substrates	Robert J. Small	08/14/2003	60937-203-PR	8317-203-888
60/509,920	Cerium Oxide Abrasives for Chemical Mechanical Polishing	Robert J. Small	10/10/2003	60937-204-PR	8317-204-888
60/516,736	Chemical Mechanical Polishing Slurries and Cleaners Containing Salicyclic Acid as a Corrosion Inhibitor	Carter, et al.	11/04/2003	60937-206-PR	8317-206-888
60/494,955	Periodic Acid Compositions for Polishing Ruthenium Substrates	Robert J. Small	08/14/2003	60937-207-PR	8317-207-888
10/683,730	Chemical Mechanical Polishing Compositions and Process	Small, et al.	10/10/2003	60937-211-US	8317-211-999
60/514,020	Alumina Abrasive for Chemical Mechanical Polishing	Philippe H. Chelle	10/27/1999	60937-213-PR	8317-213-888
60/502,951	Chemical Mechanical Polishing Slurries and Cleaners Containing Salicyclic Acid as a Corrosion Inhibitor	Tamilmani, et al.	09/16/2003	60937-214-PR	8317-214-888
10/665,417	Compositions for Chemical Mechanical Planarization of Tantalum and Tantalum Nitride	Small, et al.	09/22/2003	60937-215-US	8317-215-999
60/526,107	Alumina Abrasive for Chemical Mechanical Polishing	Chelle, et al.	12/02/2003	60937-216-PR	8317-216-888
60/509,922	Particulate or Particle-Bound Chelating Agents	Small, et al.	10/10/2003	60937-217-PR	8317-217-888
10/690,626	Particulate or Particle-Bound Chelating Agents	Small, et al.	10/23/2003	60937-217-US	8317-217-999
60/533,054	Chemical Mechanical Polishing of STI Features on Semiconductors: Water Polishing with Ceria Slurries	Yu, et al.	12/30/2003	60937-223-PR	8317-223-888
60/511,949	Removal of Post Etch Residues and Copper Contamination From Low-K Dielectrics Using Supercritical CO2 with Diketone Additives	Jerome Daviot	10/14/2003	60937-225-PR	8317-225-888
10/694,999	Method and Apparatus for Substrate Pre-Treatment	Lee, et al.	10/29/2003	60937-226-US	8317-226-999

App. #	Title	Inventor(s)	Filing Date	New Attorney Docket No.	Former Attorney Docket No.
60/515,450	Method of Chemically Mechanically Polishing Substrates	Brandon S. Scott	10/30/2003	60937-228-PR	8317-228-888